

## Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	$I_D$ max $T_A = +25^\circ\text{C}$
20V	0.45 $\Omega$ @ $V_{GS} = 4.5\text{V}$	0.6 A
	0.55 $\Omega$ @ $V_{GS} = 2.5\text{V}$	
	0.75 $\Omega$ @ $V_{GS} = 1.8\text{V}$	
	1.0 $\Omega$ @ $V_{GS} = 1.5\text{V}$	

## Description

This MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

## Features and Benefits

- Low Package Profile, 0.4mm Maximum Package Height
- 0.48mm<sup>2</sup> Package Footprint, 16 Times Smaller than SOT23
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

## Mechanical Data

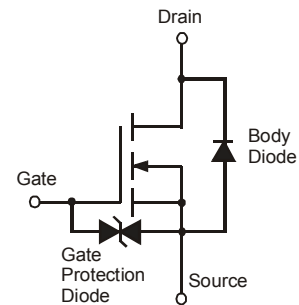
- Case: X2-DFN0806-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208④
- Weight: 0.001 grams (Approximate)



Bottom View



Top View  
Package Pin Configuration



Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2550UFA-7B	X2-DFN0806-3	10K/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



Top View  
Bar Denotes Gate and Source Side

R1 = Product Type Marking Code

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = 4.5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	0.6	A
		T <sub>A</sub> = +70°C		0.5	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	1.5	A

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P <sub>D</sub>	360	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	353	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	100	nA	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.4	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	0.28	0.45	Ω	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 200mA
		—	0.33	0.55		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 100mA
		—	0.4	0.75		V <sub>GS</sub> = 1.8V, I <sub>D</sub> = 50mA
		—	0.5	1.0		V <sub>GS</sub> = 1.5V, I <sub>D</sub> = 10mA
Diode Forward Voltage	V <sub>SD</sub>	—	—	1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 10mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	52.5	—	pF	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	6.3	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	5.2	—	pF	
Total Gate Charge	Q <sub>g</sub>	—	0.88	—	nC	V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 250mA
Gate-Source Charge	Q <sub>gs</sub>	—	0.11	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	0.10	—	nC	
Turn-On Delay Time	t <sub>D(on)</sub>	—	7.1	—	ns	V <sub>DD</sub> = 10V, V <sub>GS</sub> = 4.5V, R <sub>L</sub> = 47Ω, R <sub>G</sub> = 10Ω
Turn-On Rise Time	t <sub>r</sub>	—	11	—	ns	
Turn-Off Delay Time	t <sub>D(off)</sub>	—	105	—	ns	
Turn-Off Fall Time	t <sub>f</sub>	—	36	—	ns	

- Notes:
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
  6. Device mounted on minimum recommended pad layout test board, 10μs pulse duty cycle = 1%.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

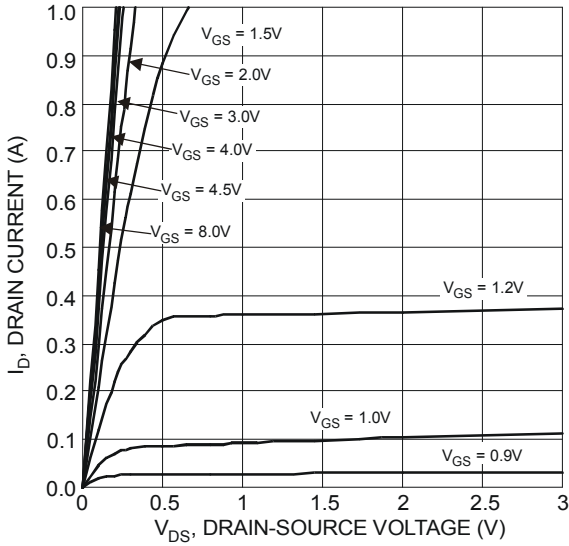


Figure 1 Typical Output Characteristics

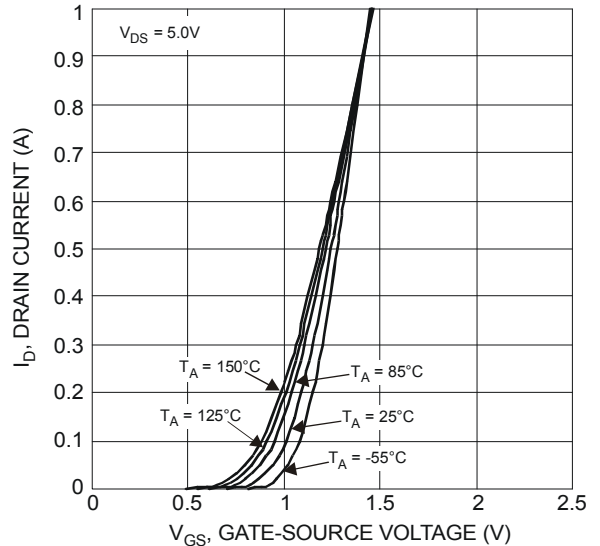


Figure 2 Typical Transfer Characteristics

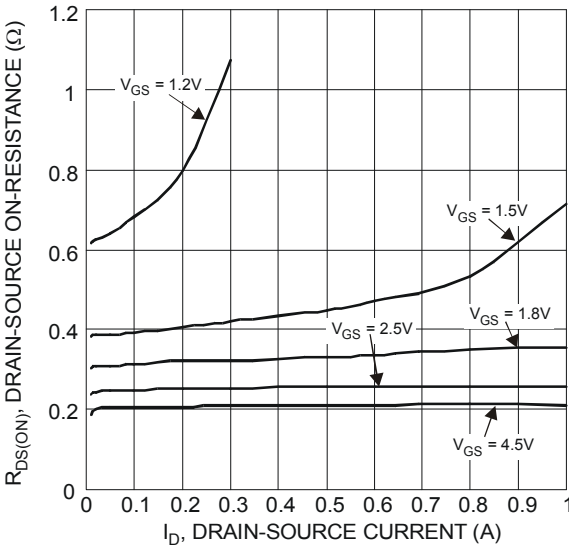


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

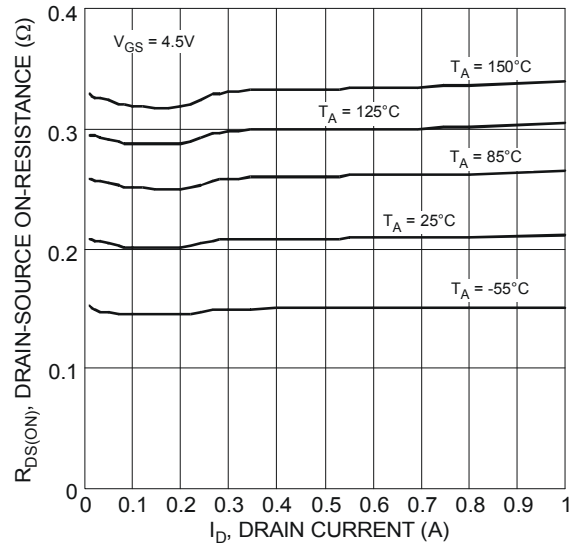


Figure 4 Typical On-Resistance vs. Drain Current and Temperature

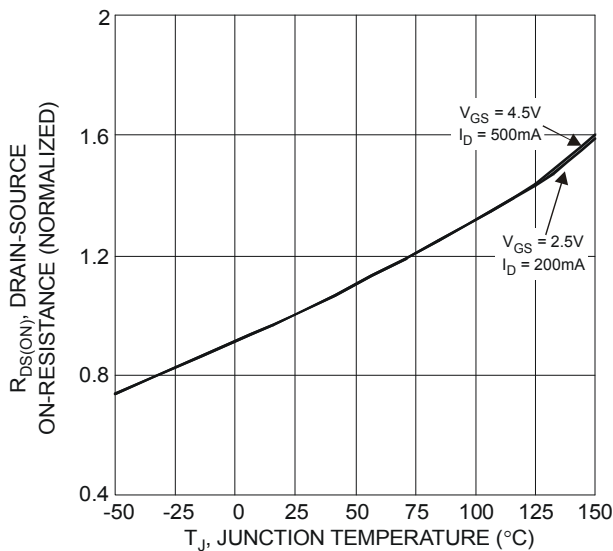


Figure 5 On-Resistance Variation with Temperature

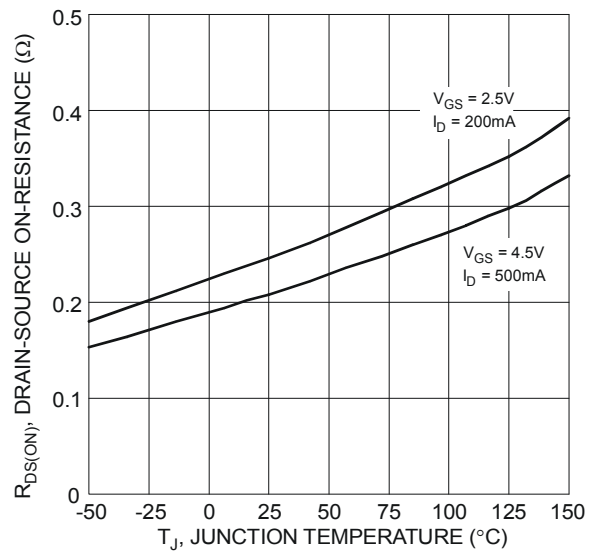


Figure 6 On-Resistance Variation with Temperature

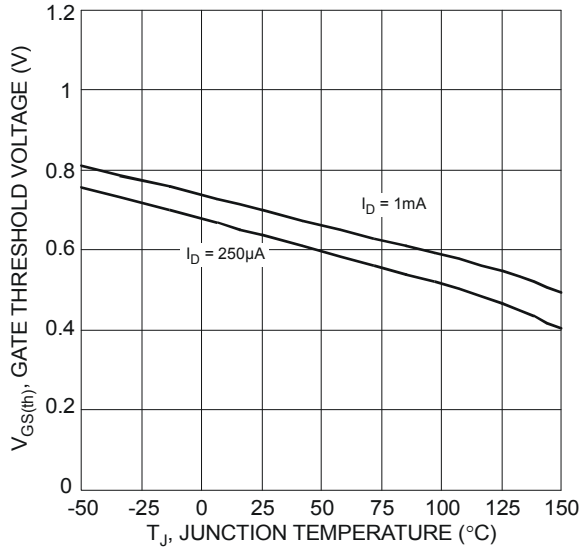


Figure 7 Gate Threshold Variation vs. Ambient Temperature

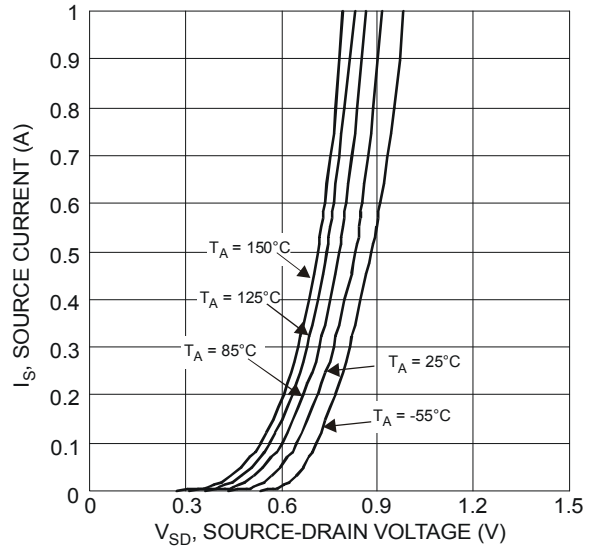


Figure 8 Diode Forward Voltage vs. Current

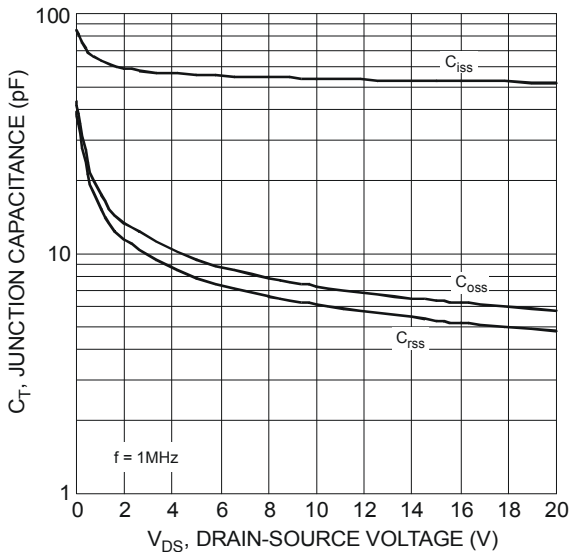


Figure 9 Typical Junction Capacitance

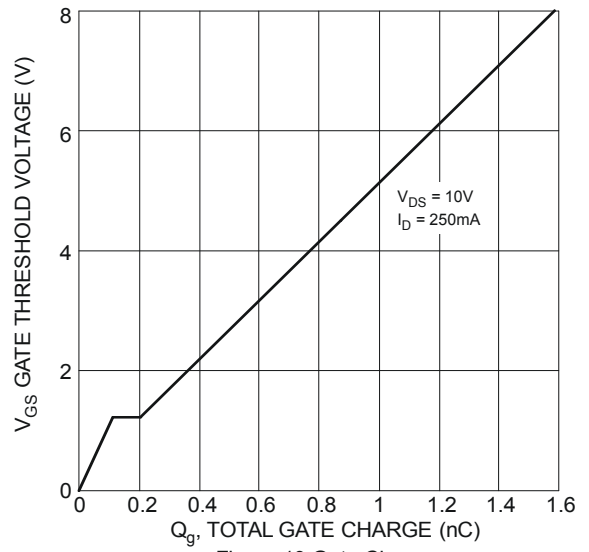


Figure 10 Gate Charge

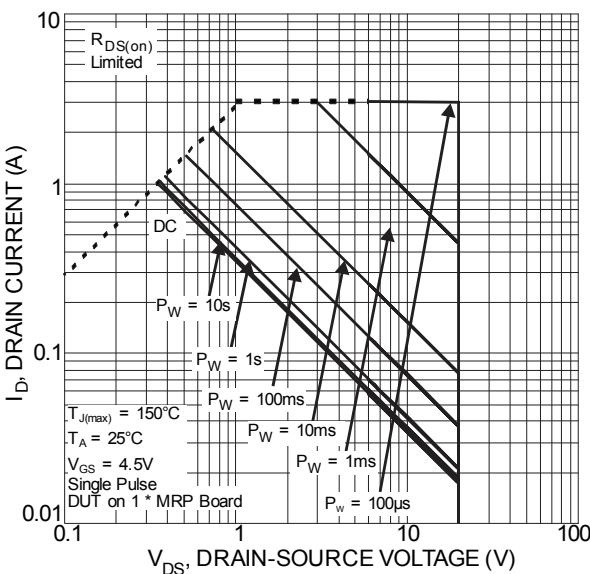
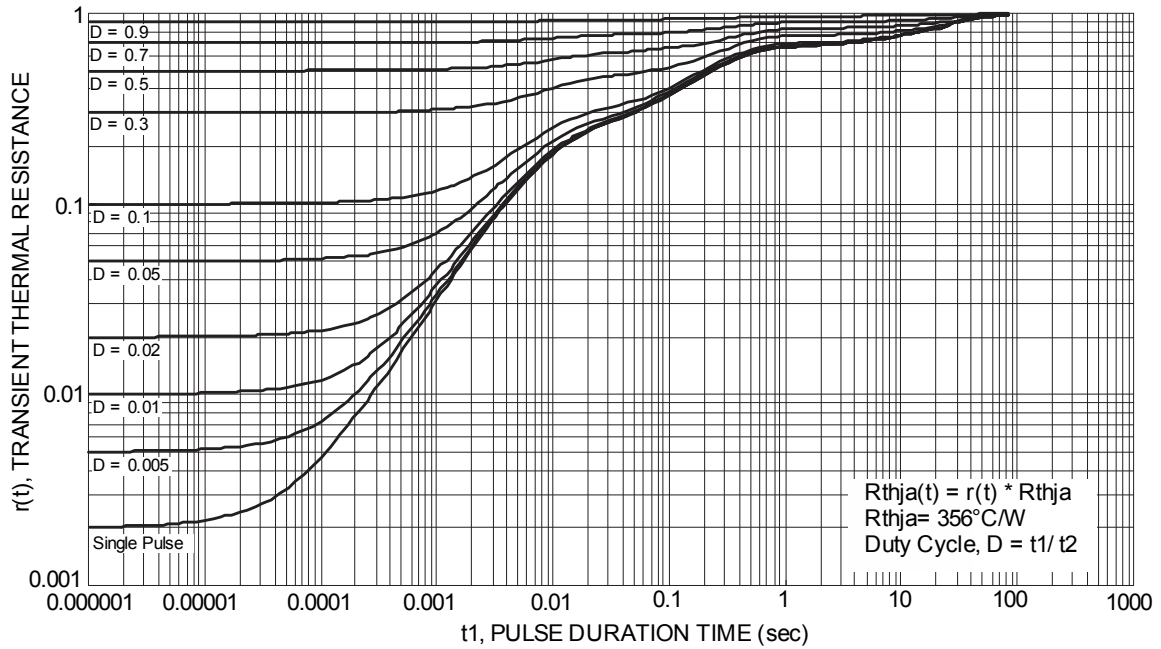
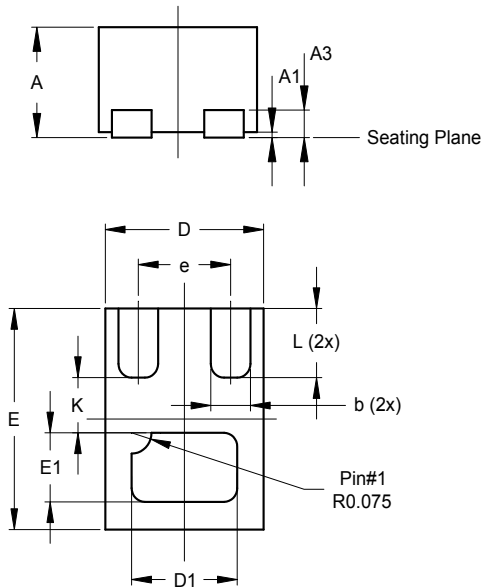


Figure 11 SOA, Safe Operation Area



### Package Outline Dimensions

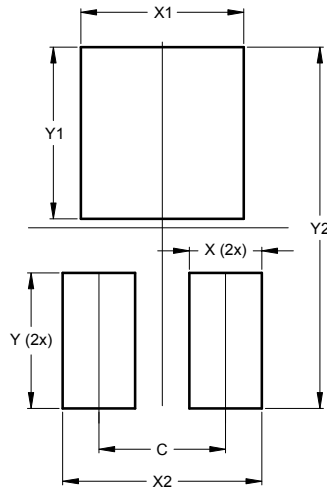
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X2-DFN0806-3			
Dim	Min	Max	Typ
A	0.375	0.40	0.39
A1	0	0.05	0.02
A3	-	-	0.10
b	0.10	0.20	0.15
D	0.55	0.65	0.60
D1	0.35	0.45	0.40
E	0.75	0.85	0.80
E1	0.20	0.30	0.25
e	-	-	0.35
K	-	-	0.20
L	0.20	0.30	0.25
All Dimensions in mm			

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
<b>C</b>	0.350
<b>X</b>	0.200
<b>X1</b>	0.450
<b>X2</b>	0.550
<b>Y</b>	0.375
<b>Y1</b>	0.475
<b>Y2</b>	1.000

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